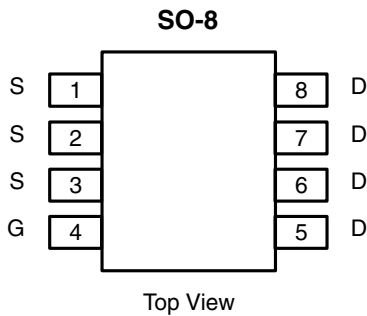


N-Channel 30 V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
30	0.0135 at V _{GS} = 10 V	13.6	7.3 nC
	0.0175 at V _{GS} = 4.5 V	12.0	



Ordering Information:
Si4714DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

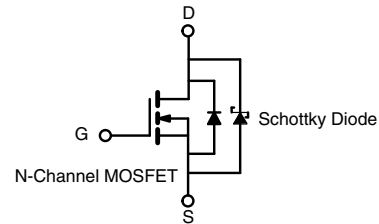
- Halogen-free According to IEC 61249-2-21 Definition
- SkyFET[®] Monolithic TrenchFET[®] Gen. III Power MOSFET and Schottky Diode
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Notebook PC
- System Power, Memory
- Buck Converter
- Synchronous Rectifier Switch



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	A
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Pulsed Drain Current (t = 300 μs)	I _{DM}	50	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	
Single Pulse Avalanche Current	I _{AS}	15	
Single Pulse Avalanche Energy	E _{AS}	11.25	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	W
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	38	50	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	22	28	

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 85 °C/W.

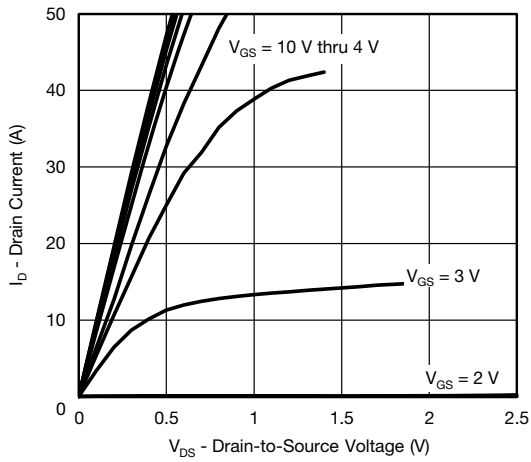
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = 1\text{ mA}$	30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1		2.3	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$		0.017	0.150	mA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$		1	10	
On -State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.0110	0.0135	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		0.0145	0.0175	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		25		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		722		pF
Output Capacitance	C_{oss}			194		
Reverse Transfer Capacitance	C_{rss}			64		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		16.3	24.5	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		7.3	11	
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			2		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.3	1.1	2.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		9	18	ns
Rise Time	t_r			18	35	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	14	
Rise Time	t_r			11	22	
Turn-Off Delay Time	$t_{d(off)}$			14	28	
Fall Time	t_f			9	18	
Drain-Source Body Diode and Schottky Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			3.8	A
Pulse Diode Forward Current ^a	I_{SM}				50	
Body Diode Voltage	V_{SD}	$I_S = 1\text{ A}$		0.42	0.53	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		14.5	29	ns
Body Diode Reverse Recovery Charge	Q_{rr}			5	10	nC
Reverse Recovery Fall Time	t_a			7.5		ns
Reverse Recovery Rise Time	t_b			7		

Notes:

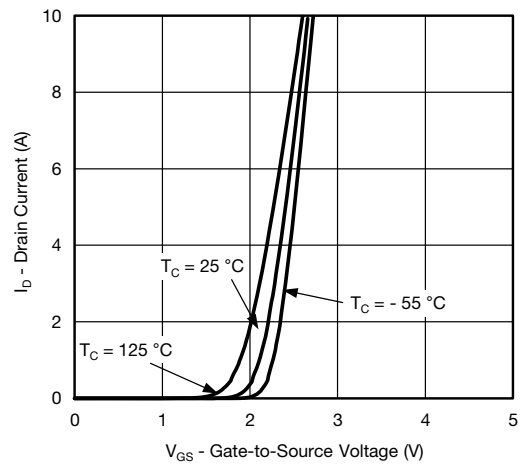
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

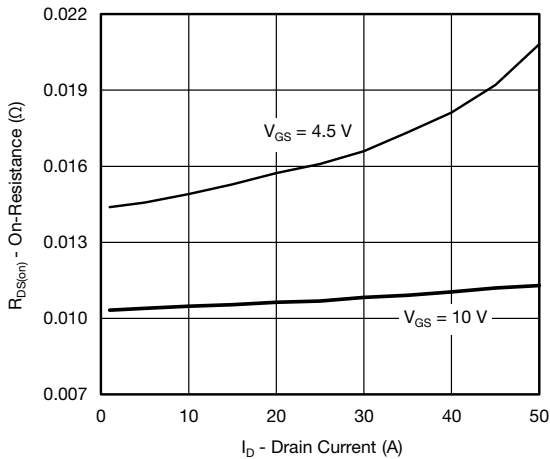
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



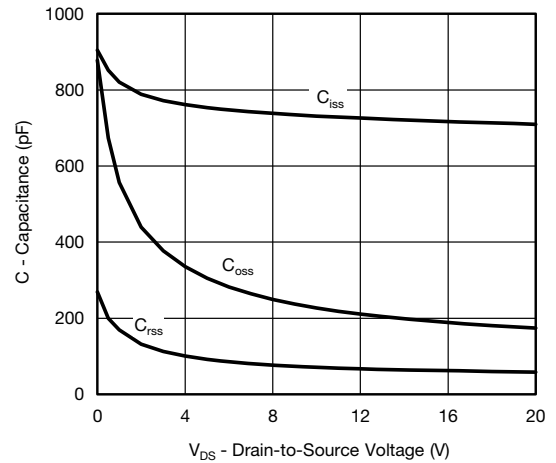
Output Characteristics



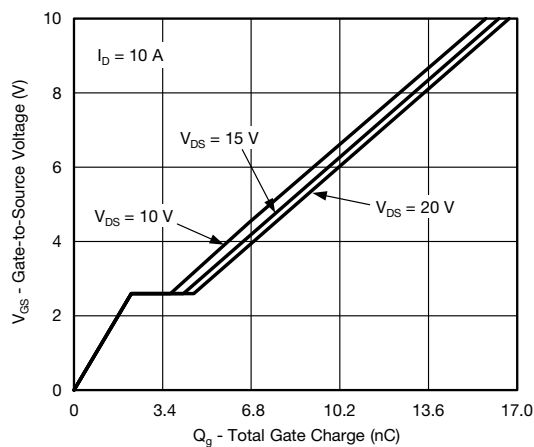
Transfer Characteristics



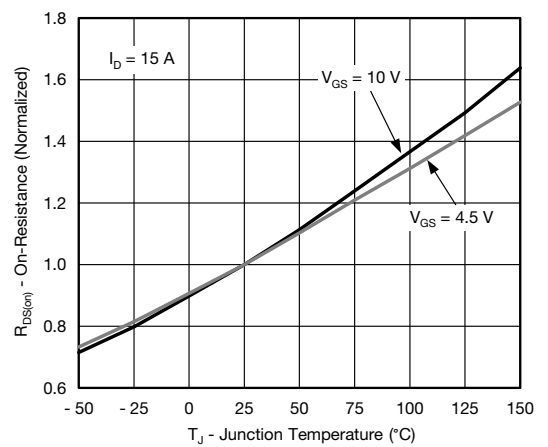
On-Resistance vs. Drain Current



Capacitance

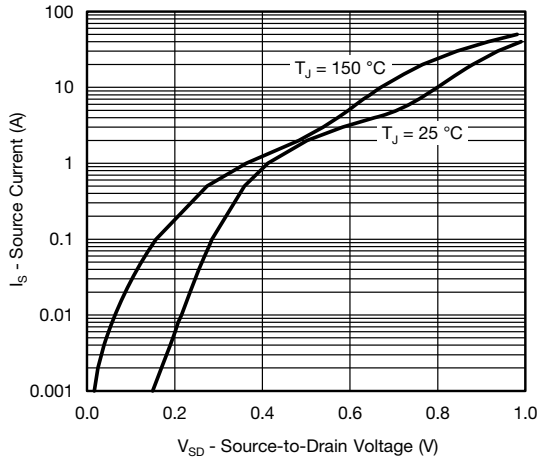


Gate Charge

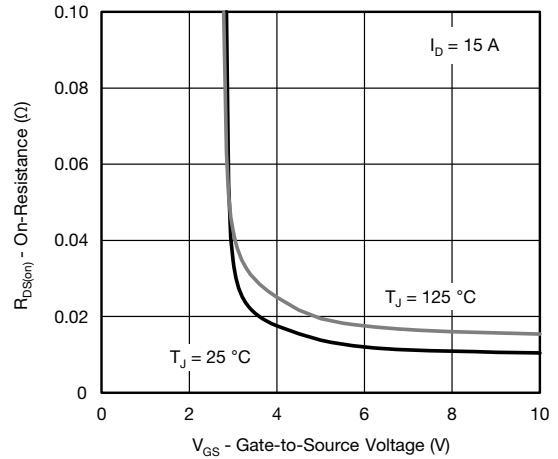


On-Resistance vs. Junction Temperature

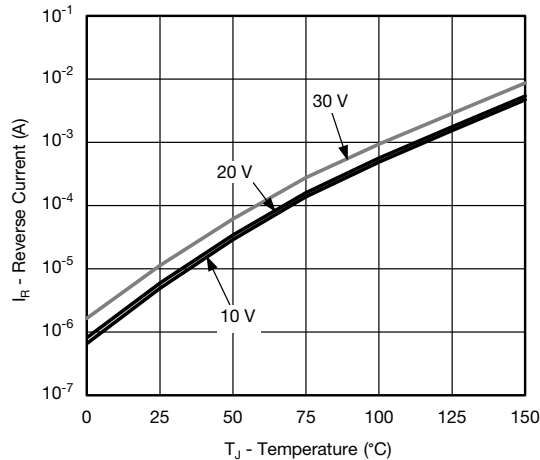
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



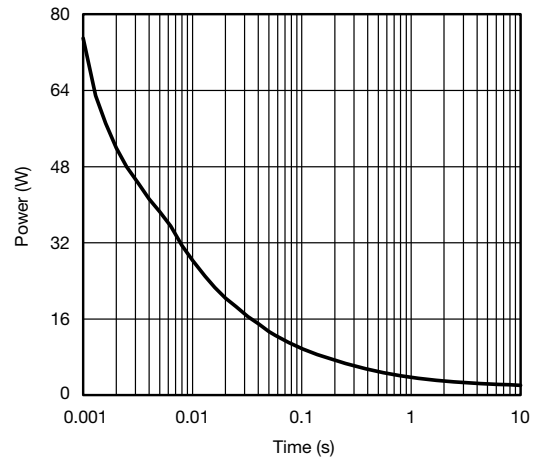
Source-Drain Diode Forward Voltage



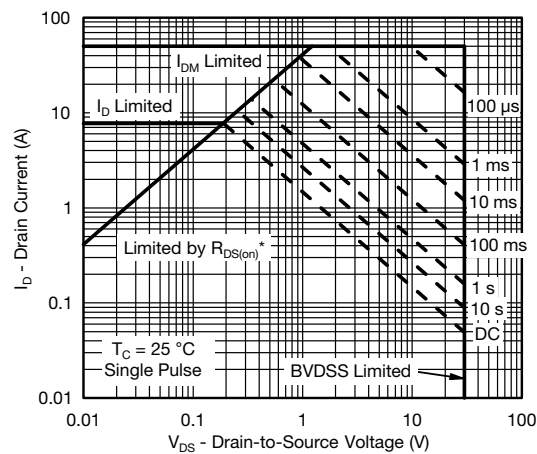
On-Resistance vs. Gate-to-Source Voltage



Reverse Current (Schottky)

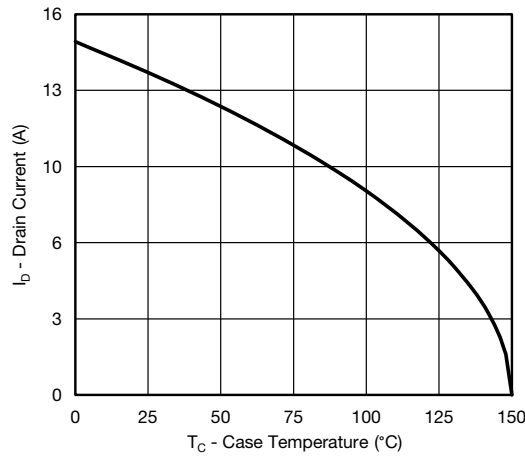


Single Pulse Power, Junction-to-Ambient

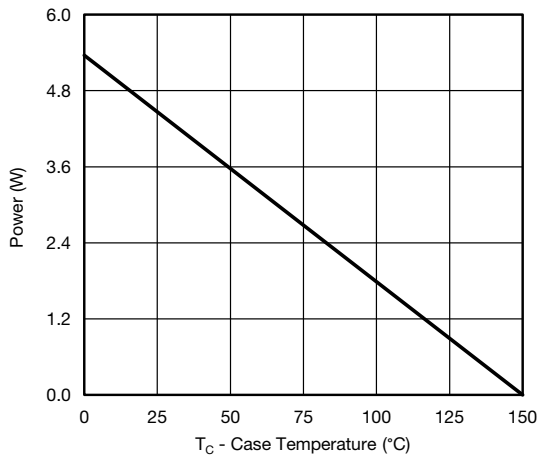


Safe Operating Area

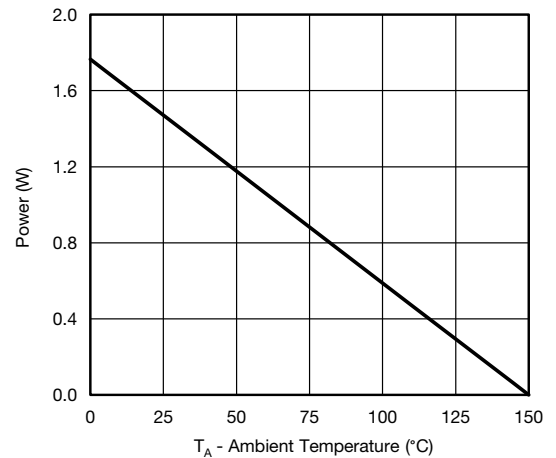
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



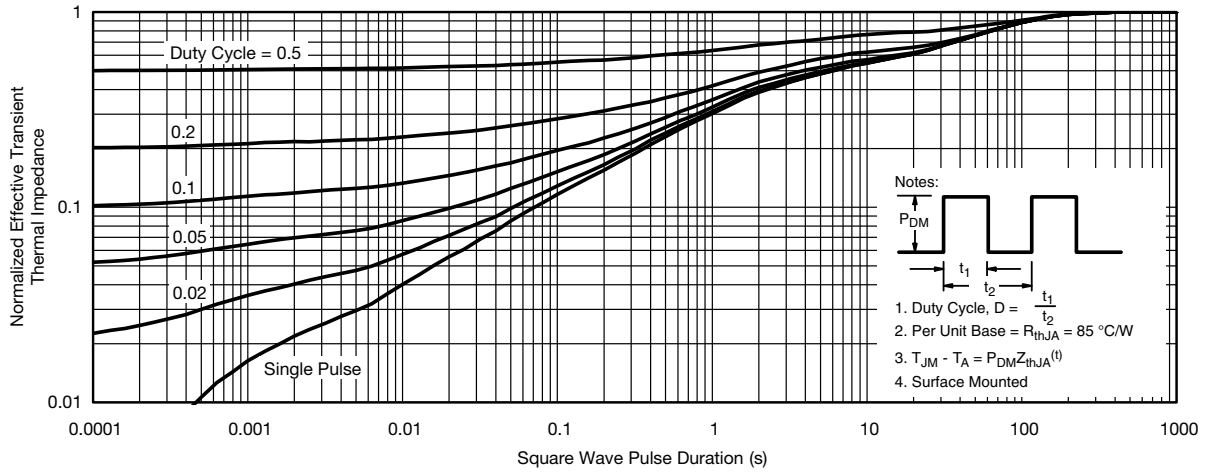
Power Derating, Junction-to-Foot



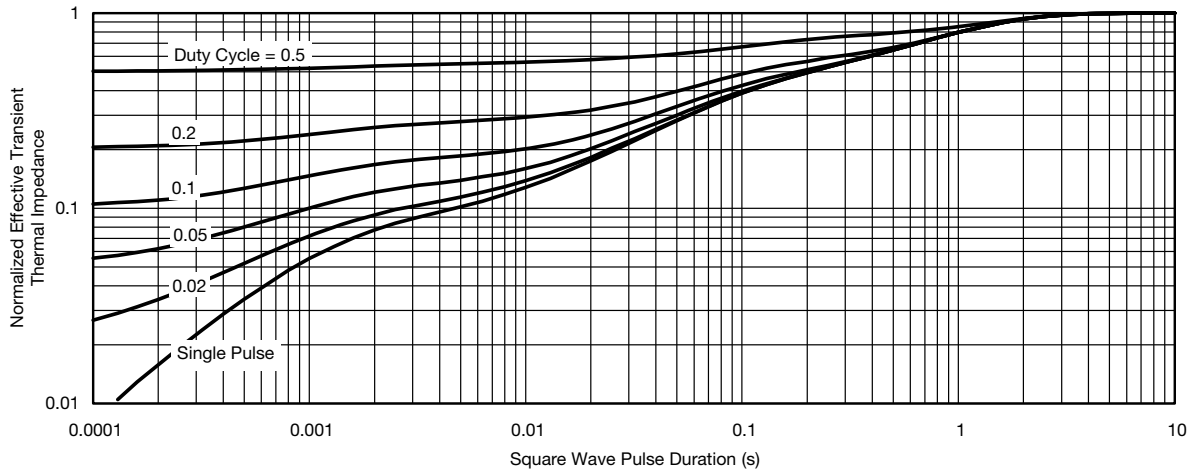
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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